

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,122,095 B2
APPLICATION NO. : 10/800252
DATED : October 17, 2006
INVENTOR(S) : Letertre et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page:

Item (56) **References Cited**, OTHER PUBLICATIONS, S. Kodama et al. reference, change "Gated Gabricated" to -- Gates Fabricated --; and delete "vol. 241ga, p. 434-435 (19099)" and insert -- Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials, Tokyo, Japan (1999), pp. 434-435. --.

Column 6:

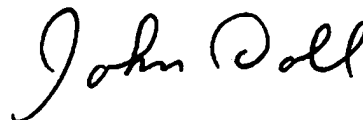
Line 37, after "The method of claim 12" delete "wherein".

Column 7:

Line 6, after "comprises a seed layer for epitaxial" insert -- growth and at least one epitaxial --.

Signed and Sealed this

Twenty-seventh Day of January, 2009



JOHN DOLL
Acting Director of the United States Patent and Trademark Office